

advanced

# High Efficiency Thyristor

$$V_{\text{DRM}} = 1200 \text{ V}$$

$$I_{\text{TAV}} = 20 \text{ A}$$

$$V_{\text{T}} = 1.4 \text{ V}$$

Triode  
 Single Reverse Conducting Thyristor

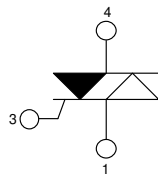
Part number

**CLA20EF1200PZ**

Marking on Product: CLA20EF1200PZ



Backside: anode



### Features / Advantages:

- Thyristor for fast turn-on switching
- Integrated free wheeling diode
- Planar passivated chip
- Long-term stability

### Applications:

- Ignition for HD lamps
- Capacity discharge

### Package: TO-263 (D2Pak-HV)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

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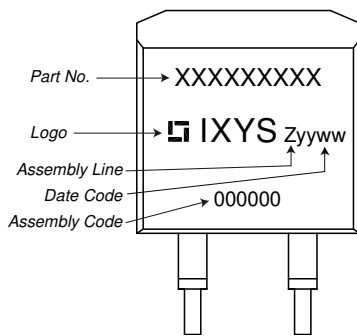


| Thyristor      |  |  |                         | Ratings |            |                  |  |
|----------------|--|--|-------------------------|---------|------------|------------------|--|
| Symbol         | Definition   | Conditions   | min.                    | typ.    | max.       | Unit             |  |
| $V_{DSM}$      | max. non-repetitive forward blocking voltage                               | $T_{VJ} = 25^{\circ}C$   |                         |         | 1300       | V                |  |
| $V_{DRM}$      | max. repetitive forward blocking voltage                                   | $T_{VJ} = 25^{\circ}C$   |                         |         | 1200       | V                |  |
| $I_D$          | drain current  | $V_D = 1200 V$   | $T_{VJ} = 25^{\circ}C$  |         | 10         | $\mu A$          |  |
|                |  | $V_D = 1200 V$   | $T_{VJ} = 125^{\circ}C$ |         | 1          | mA               |  |
| $V_T$          | forward voltage drop<br>Note:<br>reverse voltage drop $\sim 1.2 \times VT$ | $I_T = 20 A$   | $T_{VJ} = 25^{\circ}C$  |         | 1.40       | V                |  |
|                |  | $I_T = 40 A$   |                         |         | 1.60       | V                |  |
|                |  | $I_T = 20 A$   | $T_{VJ} = 125^{\circ}C$ |         | 1.40       | V                |  |
|                |  | $I_T = 40 A$   |                         |         | 1.60       | V                |  |
| $I_{TAV}$      | average forward current  | $T_C = 115^{\circ}C$<br>DC   | $T_{VJ} = 150^{\circ}C$ |         | 20         | A                |  |
| $V_{T0}$       | threshold voltage<br>slope resistance } for power loss calculation only    |  | $T_{VJ} = 150^{\circ}C$ |         | 0.90       | V                |  |
| $r_T$          |  |  |                         | 25      | m $\Omega$ |                  |  |
| $R_{thJC}$     | thermal resistance junction to case  |  |                         |         | 0.65       | K/W              |  |
| $R_{thCH}$     | thermal resistance case to heatsink  |  |                         | 0.25    |            | K/W              |  |
| $P_{tot}$      | total power dissipation  |  | $T_C = 25^{\circ}C$     |         | 190        | W                |  |
| $I_{TSM}$      | max. forward surge current   | $t = 10 ms$ ; (50 Hz), sine  | $T_{VJ} = 45^{\circ}C$  |         | 120        | A                |  |
|                |  | $t = 8,3 ms$ ; (60 Hz), sine   | $V_R = 0 V$             |         | 130        | A                |  |
|                |  | $t = 10 ms$ ; (50 Hz), sine  | $T_{VJ} = 150^{\circ}C$ |         | 100        | A                |  |
|                |  | $t = 8,3 ms$ ; (60 Hz), sine   | $V_R = 0 V$             |         | 110        | A                |  |
| $I^2t$         | value for fusing   | $t = 10 ms$ ; (50 Hz), sine  | $T_{VJ} = 45^{\circ}C$  |         | 72         | A <sup>2</sup> s |  |
|                |  | $t = 8,3 ms$ ; (60 Hz), sine   | $V_R = 0 V$             |         | 70         | A <sup>2</sup> s |  |
|                |  | $t = 10 ms$ ; (50 Hz), sine  | $T_{VJ} = 150^{\circ}C$ |         | 50         | A <sup>2</sup> s |  |
|                |  | $t = 8,3 ms$ ; (60 Hz), sine   | $V_R = 0 V$             |         | 50         | A <sup>2</sup> s |  |
| $C_J$          | junction capacitance   | $V_R = 400 V$ $f = 1 MHz$  | $T_{VJ} = 25^{\circ}C$  | 6       |            | pF               |  |
| $P_{GM}$       | max. gate power dissipation  | $t_p = 30 \mu s$   | $T_C = 150^{\circ}C$    |         | 10         | W                |  |
|                |  | $t_p = 300 \mu s$  |                         |         | 5          | W                |  |
| $P_{GAV}$      | average gate power dissipation   |  |                         |         | 0.5        | W                |  |
| $(di/dt)_{cr}$ | critical rate of rise of current   | $T_{VJ} = 150^{\circ}C$ ; $f = 50 Hz$ repetitive, $I_T = 60 A$   |                         |         | 500        | A/ $\mu s$       |  |
|                |  | $t_p = 1 \mu s$ ; $di_G/dt = 0.5 A/\mu s$ ; $I_{TSA} = 600 A$<br>$I_G = 0.07 A$ ; $V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 20 A$ |                         |         | 1500       | A/ $\mu s$       |  |
| $(dv/dt)_{cr}$ | critical rate of rise of voltage   | $V = \frac{2}{3} V_{DRM}$<br>$R_{GK} = \infty$ ; method 1 (linear voltage rise)  | $T_{VJ} = 150^{\circ}C$ |         | 500        | V/ $\mu s$       |  |
| $V_{GT}$       | gate trigger voltage   | $V_D = 6 V$  | $T_{VJ} = 25^{\circ}C$  |         | 1.3        | V                |  |
|                |  |  | $T_{VJ} = -40^{\circ}C$ |         | 1.6        | V                |  |
| $I_{GT}$       | gate trigger current   | $V_D = 6 V$  | $T_{VJ} = 25^{\circ}C$  |         | 20         | mA               |  |
|                |  |  | $T_{VJ} = -40^{\circ}C$ |         | 35         | mA               |  |
| $V_{GD}$       | gate non-trigger voltage   | $V_D = \frac{2}{3} V_{DRM}$  | $T_{VJ} = 150^{\circ}C$ |         | 0.2        | V                |  |
| $I_{GD}$       | gate non-trigger current   |  |                         |         | 1          | mA               |  |
| $I_L$          | latching current   | $t_p = 10 \mu s$   | $T_{VJ} = 25^{\circ}C$  |         | 30         | mA               |  |
|                |  | $I_G = 0.07 A$ ; $di_G/dt = 0.5 A/\mu s$   |                         |         |            |                  |  |
| $I_H$          | holding current  | $V_D = 6 V$ $R_{GK} = \infty$  | $T_{VJ} = 25^{\circ}C$  |         | 25         | mA               |  |
| $t_{gd}$       | gate controlled delay time   | $V_D = \frac{1}{2} V_{DRM}$<br>$I_G = 0.07 A$ ; $di_G/dt = 0.5 A/\mu s$  | $T_{VJ} = 25^{\circ}C$  |         | 2          | $\mu s$          |  |
| $t_q$          | turn-off time  | $V_R = 0 V$ ; $I_T = 20 A$ ; $V = \frac{2}{3} V_{DRM}$<br>$di/dt = 10 A/\mu s$ $dv/dt = 20 V/\mu s$ $t_p = 200 \mu s$                | $T_{VJ} = 125^{\circ}C$ | 150     |            | $\mu s$          |  |



| Package TO-263 (D2Pak-HV) |  | Ratings              |      |      |      |      |
|---------------------------|--|----------------------|------|------|------|------|
| Symbol                    | Definition   | Conditions           | min. | typ. | max. | Unit |
| $I_{RMS}$                 | RMS current  | per terminal         |      |      | 35   | A    |
| $T_{VJ}$                  | virtual junction temperature                                 |                      | -40  |      | 150  | °C   |
| $T_{op}$                  | operation temperature  |                      | -40  |      | 125  | °C   |
| $T_{stg}$                 | storage temperature  |                      | -40  |      | 150  | °C   |
| <b>Weight</b>             |  |                      |      | 1.5  |      | g    |
| $F_C$                     | mounting force with clip                                     |                      | 20   |      | 60   | N    |
| $d_{Spp/App}$             | creepage distance on surface / striking distance through air | terminal to terminal | 4.2  |      |      | mm   |
| $d_{Spb/Apb}$             |  | terminal to backside | 4.7  |      |      | mm   |

**Product Marking**



**Part description**

- C = Thyristor (SCR)
- L = High Efficiency Thyristor
- A = (up to 1200V)
- 20 = Current Rating [A]
- EF = Single Reverse Conducting Thyristor
- 1200 = Reverse Voltage [V]
- PZ = TO-263AB (D2Pak) (2HV)

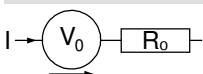
| Ordering    | Ordering Number   | Marking on Product | Delivery Mode | Quantity | Code No. |
|-------------|-------------------|--------------------|---------------|----------|----------|
| Standard    | CLA20EF1200PZ-TRL | CLA20EF1200PZ      | Tape & Reel   | 800      | 522555   |
| Alternative | CLA20EF1200PZ-TUB | CLA20EF1200PZ      | Tube          | 50       | 523762   |

| Similar Part  | Package      | Voltage class |
|---------------|--------------|---------------|
| CLA20EF1200PB | TO-220AB (3) | 1200          |

**Equivalent Circuits for Simulation**

\* on die level

$T_{VJ} = 150\text{ °C}$

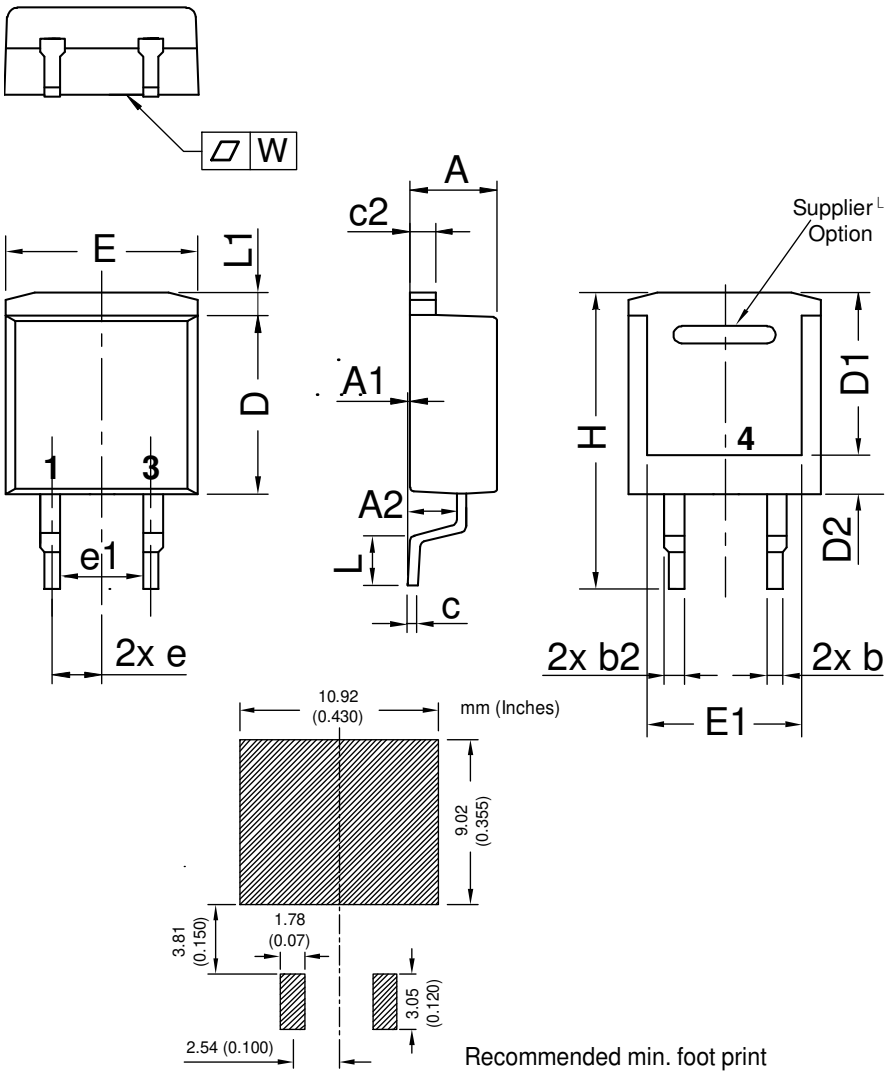


**Thyristor**

|              |                    |     |    |
|--------------|--------------------|-----|----|
| $V_{0\ max}$ | threshold voltage  | 0.9 | V  |
| $R_{0\ max}$ | slope resistance * | 22  | mΩ |

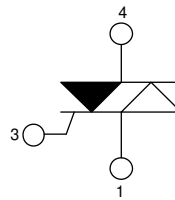


Outlines TO-263 (D2Pak-HV)



| Dim. | Millimeter |       | Inches      |       |
|------|------------|-------|-------------|-------|
|      | min        | max   | min         | max   |
| A    | 4.06       | 4.83  | 0.160       | 0.190 |
| A1   | typ. 0.10  |       | typ. 0.004  |       |
| A2   | 2.41       |       | 0.095       |       |
| b    | 0.51       | 0.99  | 0.020       | 0.039 |
| b2   | 1.14       | 1.40  | 0.045       | 0.055 |
| c    | 0.40       | 0.74  | 0.016       | 0.029 |
| c2   | 1.14       | 1.40  | 0.045       | 0.055 |
| D    | 8.38       | 9.40  | 0.330       | 0.370 |
| D1   | 8.00       | 8.89  | 0.315       | 0.350 |
| D2   | 2.3        |       | 0.091       |       |
| E    | 9.65       | 10.41 | 0.380       | 0.410 |
| E1   | 6.22       | 8.50  | 0.245       | 0.335 |
| e    | 2,54 BSC   |       | 0,100 BSC   |       |
| e1   | 4.28       |       | 0.169       |       |
| H    | 14.61      | 15.88 | 0.575       | 0.625 |
| L    | 1.78       | 2.79  | 0.070       | 0.110 |
| L1   | 1.02       | 1.68  | 0.040       | 0.066 |
| W    | typ. 0.02  | 0.040 | typ. 0.0008 | 0.002 |

All dimensions conform with and/or within JEDEC standard.





**Thyristor**



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- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

**Телефон:** 8 (812) 309 58 32 (многоканальный)

**Факс:** 8 (812) 320-02-42

**Электронная почта:** [org@eplast1.ru](mailto:org@eplast1.ru)

**Адрес:** 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.